Preferred Device

Amplifier Transistors

NPN Silicon

Features

- Pb-Free Packages are Available*
- Device Marking: Device Type, e.g., 2N5550, Date Code

MAXIMUM RATINGS

Rating	Symbol	2N5550	2N5551	Unit
Collector – Emitter Voltage	V _{CEO}	140	160	Vdc
Collector – Base Voltage	V _{CBO}	160	180	Vdc
Emitter – Base Voltage	V _{EBO}	6.0		Vdc
Collector Current – Continuous	I _C	600		mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0		mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12		W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150		°C

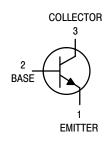
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W



http://onsemi.com







2N5550/D

Specific Device Code 55xx = Year WW = Work Week

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS		1		•	·
Collector-Emitter Breakdown Voltage (Note 1)		V _{(BR)CEO}			Vdc
$(I_C = 1.0 \text{ mAdc}, I_B = 0)$	2N5550	(, , , , , , , , , , , , , , , , , , ,	140	_	
	2N5551		160	-	
Collector-Base Breakdown Voltage		V _{(BR)CBO}			Vdc
$(I_C = 100 \mu\text{Adc}, I_E = 0)$	2N5550		160	_	
	2N5551		180	_	
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	6.0	_	Vdc
(I _E = 10 μAdc, I _C = 0)					
Collector Cutoff Current	01/5550	I _{CBO}		400	
$(V_{CB} = 100 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 120 \text{ Vdc}, I_E = 0)$	2N5550 2N5551		-	100 50	nAdc
$(V_{CB} = 120 \text{ VdC}, I_{E} = 0)$ $(V_{CB} = 100 \text{ VdC}, I_{E} = 0, T_{A} = 100^{\circ}\text{C})$	2N5550		_	100	μAdc
$(V_{CB} = 100 \text{ Vdc}, I_{E} = 0, T_{A} = 100 \text{ C})$ $(V_{CB} = 120 \text{ Vdc}, I_{E} = 0, T_{A} = 100 \text{ C})$	2N5551		_	50	μπασ
Emitter Cutoff Current		Irno	_	50	nAdc
$(V_{EB} = 4.0 \text{ Vdc}, I_{C} = 0)$		I _{EBO}	_	30	IIAGC
ON CHARACTERISTICS (Note 1)				<u> </u>	
DC Current Gain		h		I	
(I _C = 1.0 mAdc, V _{CE} = 5.0 Vdc)	2N5550	h _{FE}	60	_	_
(1C = 1.0 HIAdo, VCE = 5.0 Vdc)	2N5551		80	_	
$(I_C = 10 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$	2N5550		60	250	
	2N5551		80	250	
$(I_C = 50 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$	2N5550		20	_	
(.C == (as, .CE = (as)	2N5551		30	-	
Collector-Emitter Saturation Voltage		V _{CE(sat)}			Vdc
$(I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc})$	Both Types	02(001)	-	0.15	
(1 50 41 1 50 41)	01/5550			0.05	
$(I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc})$	2N5550 2N5551		-	0.25 0.20	
	2110001			0.20	
Base – Emitter Saturation Voltage	Dath Tones	V _{BE(sat)}		4.0	Vdc
$(I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc})$	Both Types		_	1.0	
$(I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc})$	2N5550		_	1.2	
	2N5551		_	1.0	
SMALL-SIGNAL CHARACTERISTICS				•	!
Current-Gain — Bandwidth Product		f _T	100	300	MHz
$(I_C = 10 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 100 \text{ MHz})$		'			
Output Capacitance		C _{obo}	_	6.0	pF
$(V_{CB} = 10 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$,
Input Capacitance		C _{ibo}			pF
$(V_{EB} = 0.5 \text{ Vdc}, I_{C} = 0, f = 1.0 \text{ MHz})$	2N5550		_	30	
	2N5551			20	
Small–Signal Current Gain		h _{fe}	50	200	_
$(I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ kHz})$					
Noise Figure		NF			dB
$(I_C = 250 \mu Adc, V_{CE} = 5.0 Vdc, R_S = 1.0 kΩ,$	2N5550		-	10	
f = 1.0 kHz	2N5551		-	8.0	

^{1.} Pulse Test: Pulse Width $\leq 300~\mu\text{s},~\text{Duty Cycle} \leq 2.0\%.$

ORDERING INFORMATION

Device	Package	Shipping [†]	
2N5550	TO-92	5,000 Unit / Bulk	
2N5550RLRA	TO-92	2,000 Tape & Reel	
2N5550RLRP	TO-92	2,000 Tape & Ammo Box	
2N5550RLRPG	TO-92 (Pb-Free)	2,000 Tape & Ammo Box	
2N5551	TO-92	5,000 Unit / Bulk	
2N5551G	TO-92 (Pb-Free)	5,000 Unit / Bulk	
2N5551RL1	TO-92	2,000 Tape & Reel	
2N5551RLRA	TO-92	2,000 Tape & Reel	
2N5551RLRM	TO-92	2,000 Tape & Ammo Box	
2N5551RLRP	TO-92	2,000 Tape & Ammo Box	
2N55551ZL1	TO-92	2,000 Tape & Ammo Box	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

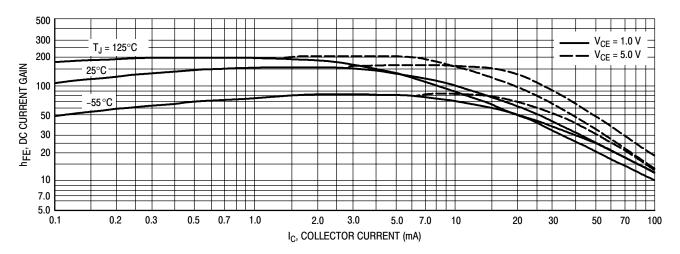


Figure 1. DC Current Gain

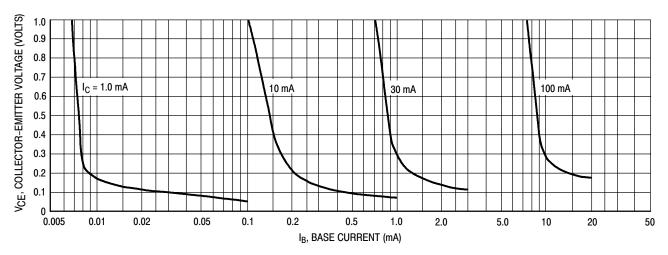


Figure 2. Collector Saturation Region

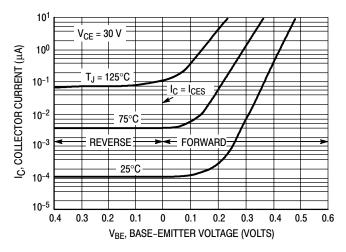


Figure 3. Collector Cut-Off Region

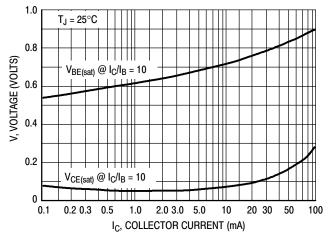


Figure 4. "On" Voltages

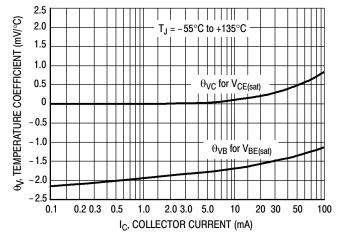
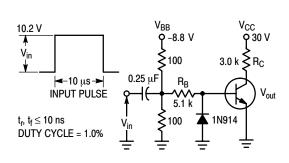


Figure 5. Temperature Coefficients



Values Shown are for I_C @ 10 mA

Figure 6. Switching Time Test Circuit

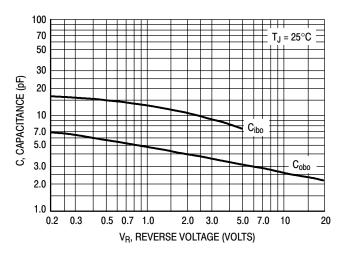


Figure 7. Capacitances

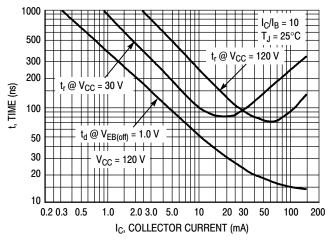


Figure 8. Turn-On Time

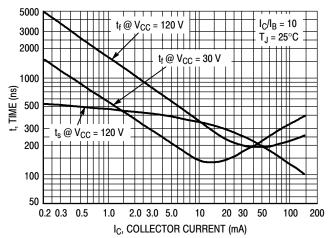
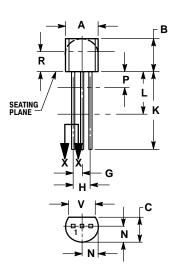


Figure 9. Turn-Off Time

PACKAGE DIMENSIONS

TO-92 **TO-226AA** CASE 29-11 **ISSUE AL**





- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 114-30M, 1902.
 CONTROLLING DIMENSION: INCH.
 CONTOUR OF PACKAGE BEYOND DIMENSION R
 IS UNCONTROLLED.
 LEAD DIMENSION IS UNCONTROLLED IN P AND
- BEYOND DIMENSION K MINIMUM.

	INCHES		INCHES MILLIN		IETERS	
DIM	MIN	MAX	MIN	MAX		
Α	0.175	0.205	4.45	5.20		
В	0.170	0.210	4.32	5.33		
С	0.125	0.165	3.18	4.19		
D	0.016	0.021	0.407	0.533		
G	0.045	0.055	1.15	1.39		
Н	0.095	0.105	2.42	2.66		
J	0.015	0.020	0.39	0.50		
K	0.500		12.70			
L	0.250		6.35			
N	0.080	0.105	2.04	2.66		
Р		0.100		2.54		
R	0.115		2.93			
٧	0.135		3.43			

STYLE 1:

PIN 1. EMITTER

COLLECTOR

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